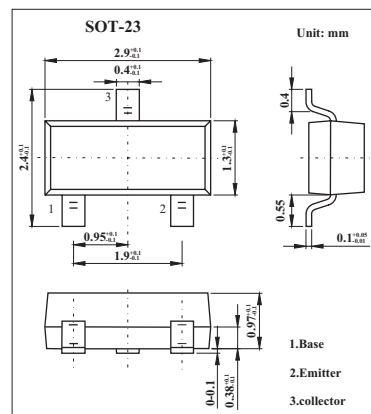


Silicon NPN Epitaxial

2SC2618

■ Features

- Low frequency amplifier.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	35	V
Collector-emitter voltage	V_{CEO}	35	V
Emitter-base voltage	V_{EBO}	4	V
Collector current	I_C	500	mA
Collector dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}$, $I_E = 0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}$, $R_{BE} = \infty$	35			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}$, $I_C = 0$	4			V
Collector cutoff current	I_{CBO}	$V_{CB} = 20\text{V}$, $I_C = 0$			0.5	μA
DC current gain	h_{FE1}	$V_{CE} = 3\text{V}$, $I_C = 10\text{mA}$	100		320	
	h_{FE2}	$V_{CE} = 3\text{V}$, $I_C = 500\text{mA}$	10			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 150\text{mA}$, $I_B = 15\text{mA}$		0.2	0.6	V
Base-emitter voltage	V_{BE}	$V_{CE} = 3\text{V}$, $I_C = 10\text{mA}$		0.64		V

■ h_{FE} Classification

Marking	RC	RD
h_{FE}	100~200	160~320